



ZXMS6005DG

60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE IntelliFET MOSFET

## **Product Summary**

- Continuous Drain Source Voltage 60V
- On-state Resistance 200mΩ
- Nominal Load Current ( $V_{IN} = 5V$ ) 2.0A
- Clamping Energy 490mJ

## Description

The ZXMS6005DG is a self protected low side IntelliFET<sup>TM</sup> MOSFET with logic level input. It integrates over-temperature, over-current, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6005DG is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

### Applications

### Lamp Driver

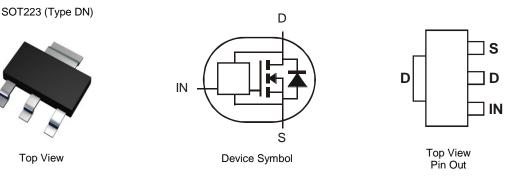
- Motor Driver
- Relay Driver
- Solenoid Driver

#### **Features and Benefits**

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Over-current Protection
  Input Protection (ESD)
- Input Protection (ESD)
- High Continuous Current Rating
  Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXMS6005DGQ)

#### **Mechanical Data**

- Case: SOT223 (Type DN)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.112 grams (Approximate)



### Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXMS6005DGTA	ZXMS6005D	7	12	1,000 Units

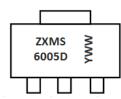
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

2. See https://www.uodes.com/quaity/read-nee/ for more mormation about blodes incorporated sidenimitors of Halogen- and Antimony-nee, "Green a Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



 $\begin{array}{l} \text{ZXMS6005D} = \text{Product Type Marking Code} \\ \text{YWW} = \text{Date Code Marking} \\ \text{Y or } \overline{\text{Y}} = \text{Last Digit of Year (ex: 8 = 2018)} \\ \text{WW or } \overline{\text{WW}} = \text{Week Code (01 to 53)} \end{array}$ 

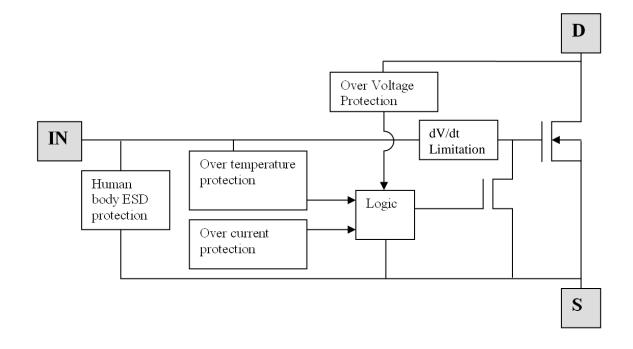
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## **Functional Block Diagram**



### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Continuous Drain-Source Voltage	V <sub>DS</sub>	60	V	
Drain-Source Voltage for Short Circuit Protection	V <sub>DS(SC)</sub>	24	V	
Continuous Input Voltage	V <sub>IN</sub>	-0.5 to +6	V	
Continuous Input Current @-0.2V $\leq V_{IN} \leq 6V$	1	No limit	mA	
Continuous Input Current $@V_{IN} < -0.2V$ or $V_{IN} > 6V$	lin	I <sub>IN</sub>   ≤2	ma	
Pulsed Drain Current @V <sub>IN</sub> = 3.3V	I <sub>DM</sub>	5	A	
Pulsed Drain Current @V <sub>IN</sub> = 5V	I <sub>DM</sub>	6	A	
Continuous Source Current (Body Diode) (Note 5)	Is	2.5	A	
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	10	A	
Unclamped Single Pulse Inductive Energy,	Г	490	mJ	
$T_J = +25^{\circ}C, I_D = 0.5A, V_{DD} = 24V$	E <sub>AS</sub>	490	mJ	
Electrostatic Discharge (Human Body Model)	V <sub>ESD</sub>	4000	V	
Charged Device Model	V <sub>CDM</sub>	1000	V	

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^{\circ}C$ (Note 5) Linear Derating Factor	PD	1.3 10.4	W mW/°C
Power Dissipation at $T_A = +25^{\circ}C$ (Note 6) Linear Derating Factor	PD	3.0 24	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	96	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	42	°C/W
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	12	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

Notes:

5. For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR-4 board, in still air conditions. 6. For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions.

7. Thermal resistance between junction and the mounting surfaces of drain and source pins.

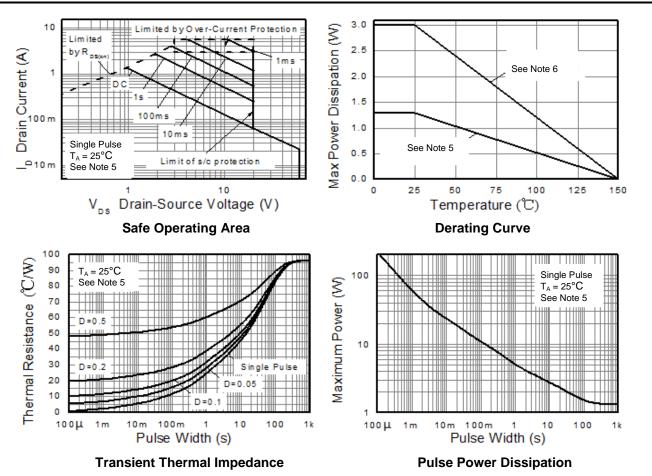


## **Recommended Operating Conditions**

The ZXMS6005DG is optimized for use with  $\mu C$  operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	VIN	0	5.5	V
Ambient Temperature Range	T <sub>A</sub>	-40	+125	°C
High Level Input Voltage for MOSFET to be on	VIH	3	5.5	V
Low Level Input Voltage for MOSFET to be off	VIL	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	VP	0	24	V

## **Thermal Characteristics**





# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

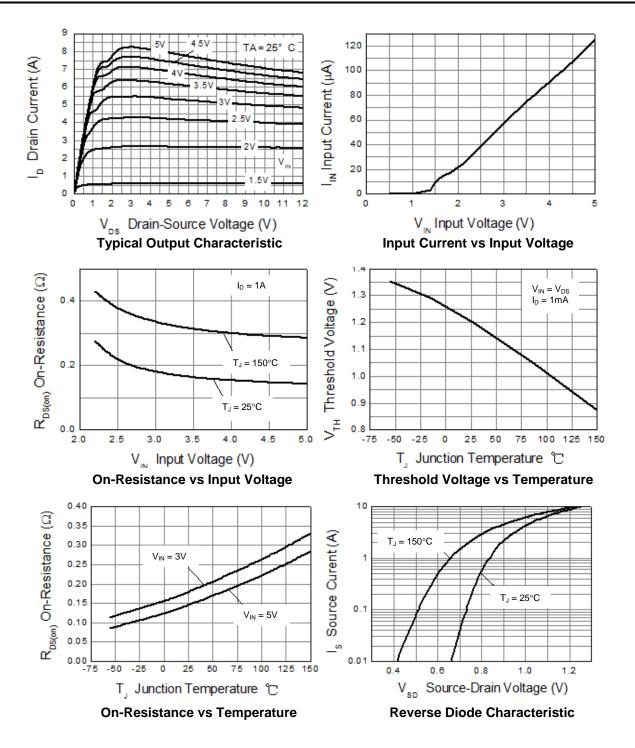
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						•
Drain-Source Clamp Voltage	V <sub>DS(AZ)</sub>	60	65	70	V	$I_D = 10 \text{mA}$
Off State Drain Current		_	—	1	μA	$V_{DS} = 12V, V_{IN} = 0V$
On State Drain Current	IDSS	_	—	2		$V_{DS} = 36V, V_{IN} = 0V$
Input Threshold Voltage	V <sub>IN(TH)</sub>	0.7	1.2	1.5	V	$V_{DS} = V_{GS}, I_D = 1mA$
Input Current			60	100	μA	$V_{IN} = 3V$
Input Current	I <sub>IN</sub>	_	120	200		$V_{IN} = 5V$
Input Current While Over Temperature Active	—		—	300	μA	$V_{IN} = 5V$
Static Drain-Source On-State Resistance	Р		170	250	mΩ	$V_{IN} = 3V$ , $I_D = 1A$
	R <sub>DS(ON)</sub>		150	200		$V_{IN} = 5V, I_D = 1A$
Continuous Drain Current (Note 5)	– I <sub>D</sub>	1.4		—	A	$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 5)		1.6	—	—		$V_{IN} = 5V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 6)		1.9		—		$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 8)		2.0		—		$V_{IN} = 5V, T_A = +25^{\circ}C$
Current Limit (Note 8)	I <sub>D(LIM)</sub>	2.2	5	—	A	$V_{IN} = 3V$
		3.3	7	—		$V_{IN} = 5V$
Dynamic Characteristics			-	-	-	
Turn On Delay Time	t <sub>D(ON)</sub>		6	—		$V_{DD} = 12V, I_D = 1A, V_{GS} = 5V$
Rise Time	t <sub>R</sub>		14	—		
Turn Off Delay Time	t <sub>D(OFF)</sub>		34	—	μs	
Fall Time	tF	_	19	_		
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 9)	T <sub>JT</sub>	+150	+175	—	°C	—
Thermal Hysteresis (Note 9)	f <sub>f</sub>	_	+10	—	°C	—

Notes: 8. The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

9. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

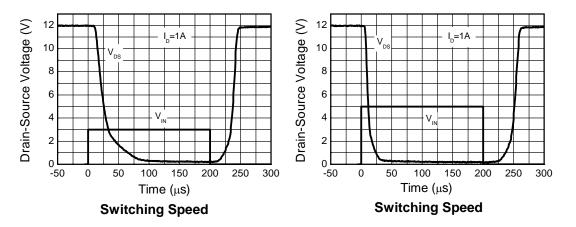


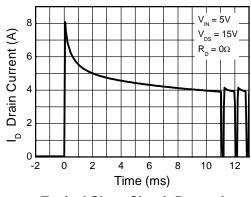
## **Typical Characteristics**





# Typical Characteristics (Cont.)





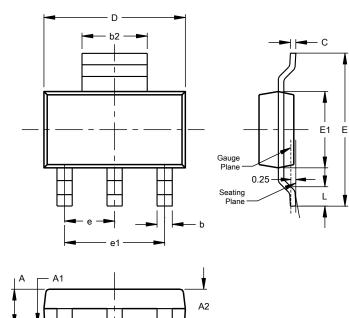
**Typical Short Circuit Protection** 



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)

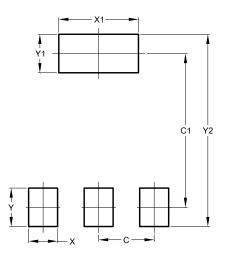


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
ш	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All C	All Dimensions in mm				

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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